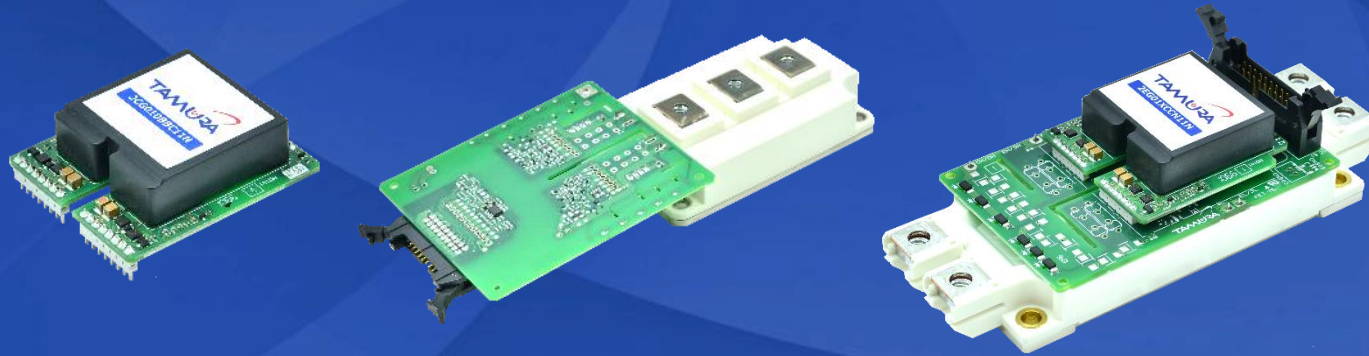


Gate drivers that bring out the performance of Infineon Technologies AG / SiC Power Modules



SUSTAINABLE
DEVELOPMENT
GOALS

Supported by Infineon Technologies AG

TAMURA
Your One and Only Company

Index

1) Gate drivers that bring out the performance of Infineon Technologies AG / SiC Power Modules

- 1-1. When, Why, we started development gate drivers
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- 1-4. Features of Gate Driver Modules
- 1-5. Gate drive waveform of 2 pulse test / Short circuit test
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- 1-7. Product Line-up for EconoDUAL™ and 62mm type

2) Introduction of One Tamura

Appendix) Contact person

Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules

1-1. Why ??



**Transformer
Technology**



**Circuit
design
Technology**



**Potting
Technology**



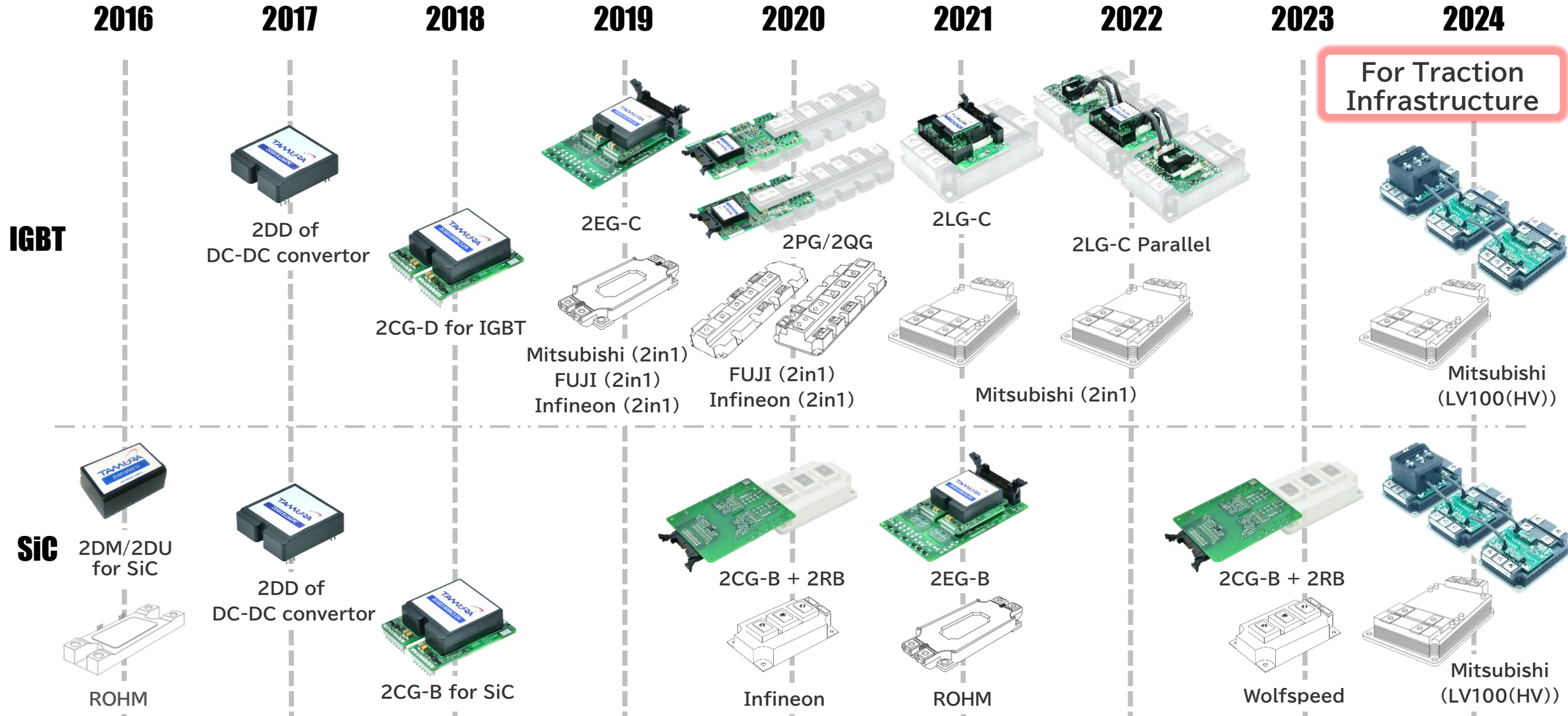
**EMI/EMC
Solution**



**Market
Awareness**

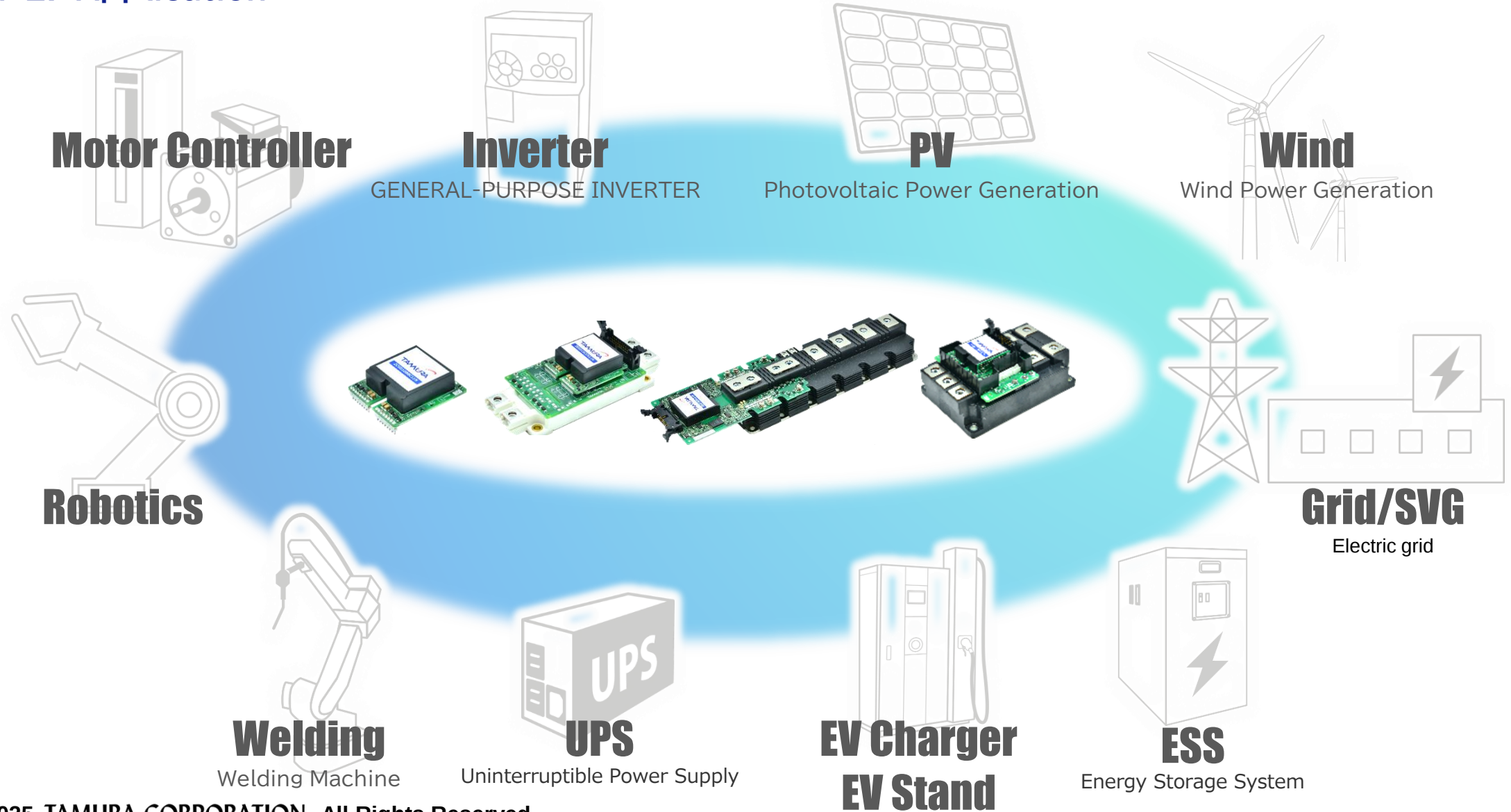
Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules

1-1. When ??



Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules

1-2. Application



Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules

1-3. Product Configuration

Product

DC/DC Converter

Gate Driver Module

Gate Driver Unit

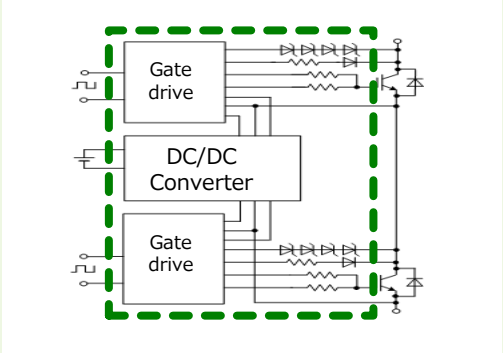
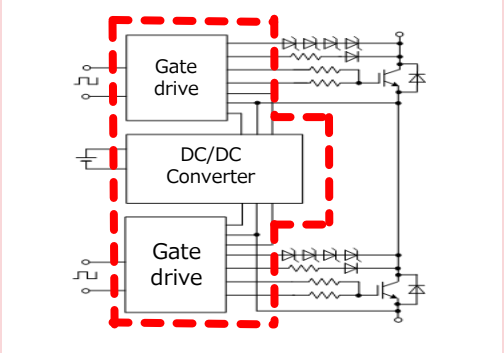
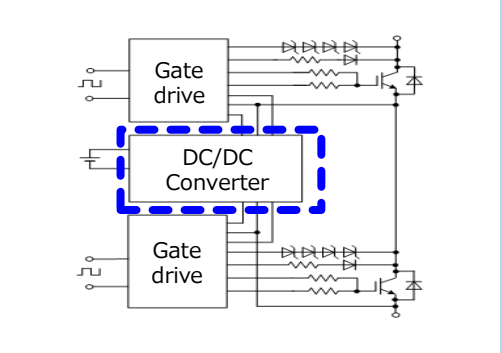
Function

**2in1 PM designated
DC/DC Converter**

**DC/DC Converter
+ Gate drive**

**Gate Driver Module
+ Gate resistors
Protective function**

Block diagram



Appearance



2DD series



2CG-B/D series



1-4. Features of Gate Driver Modules

Features of All-SiC Power Module

Feature① Short circuit tolerance is lower than Si

Feature② Low threshold voltage $V_{GS(th)}$ (1V~3V)

Feature③ $V_{GS}(+)$:On resistance does not decrease at 15V
 $V_{GS}(-)$:Low tolerance (Less than -7V)

Feature④ dV/dt can be set high

Feature⑤ High frequency operation is possible

Gate Driver
Module
solves all
problems!

Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules

1-4. Features of Gate Driver Modules

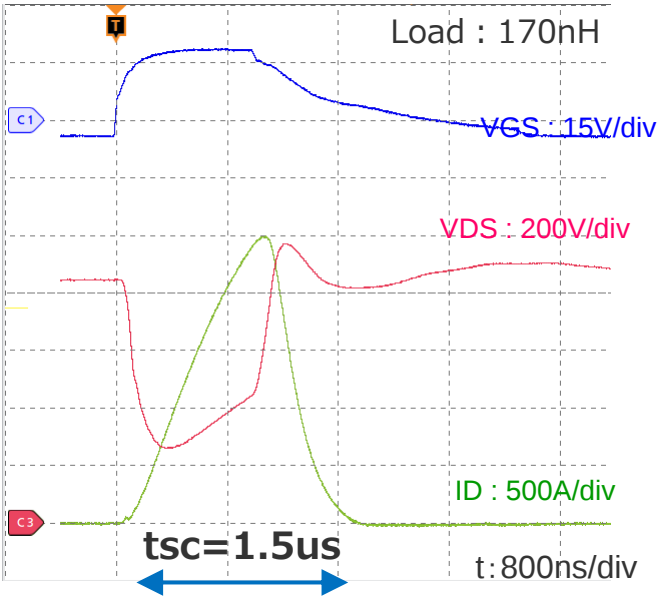
Feature ① Short circuit tolerance is lower than Si

----- Small chip area -----

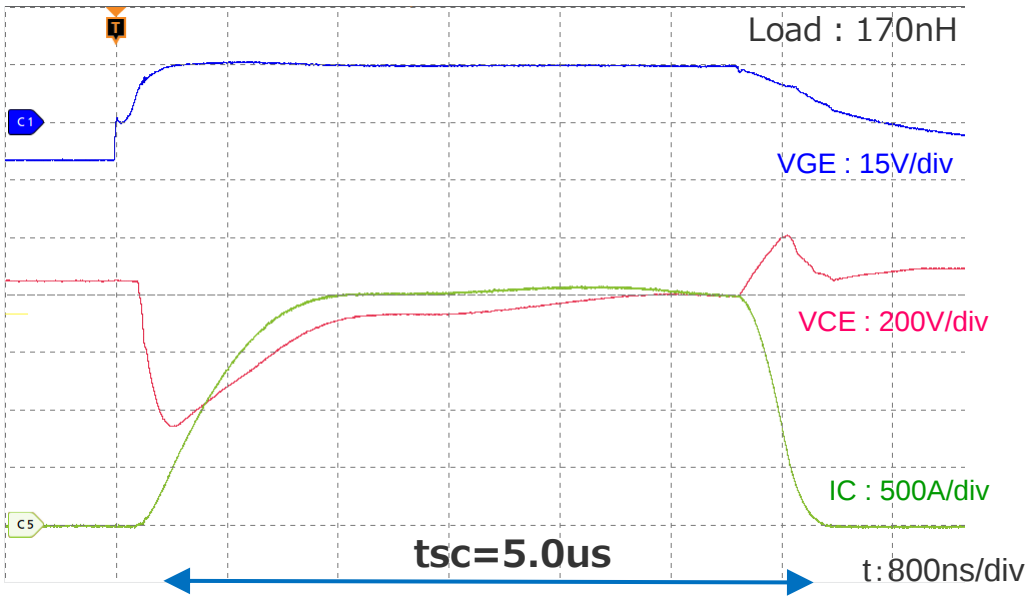
- Wide band gap
- High breakdown voltage
- High temperature operation

Support with a gate driver ... Short-circuit mask time (tsc) adjustment function

SiC power module (1200V 300A)
Waveform with shorted load



IGBT power module (1200V 300A)
Waveform with shorted load



Adjustable with external capacitor capacity

Optimal value of SiC : 1.0~3.0us

Optimal value of IGBT : 3.0~7.0us

Feature② Low threshold voltage V_{GS} (th)
(1V~3V)

--- IGBT is 6V~7V --- Beware of malfunctions from IGBT

Reduction of parasitic capacitance

The diagram illustrates a driver circuit for a SiC MOSFET. It includes a **Controller**, a **2DD (DC/DC)** converter, and two **Driver** stages. The circuit is designed to minimize parasitic capacitance, which is indicated by red dashed lines and arrows. The output of the driver is connected to the MOSFET gate, which is also connected to a load. The MOSFET is shown in a switching state, with a **dV/dt** waveform. A warning icon and the text **No malfunction at high dV/dt** are present.

No malfunction at high dV/dt

Inoise

Inoise = Cstray X dV/dt

SiC 1200V / 300A

No malfunctions !

GOOD!

dV/dt = 15KV/us

ID : 100A/div

VDS : 200V/div

t : 100ns/div

The waveform shows the switching behavior of the SiC MOSFET. The **VGSL** (gate-source voltage) is shown as a blue trace, and the **VGSH** (gate-source voltage) is shown as a blue trace. The **VDS** (drain-source voltage) is shown as a red trace, and the **ID** (drain current) is shown as a green trace. The **dV/dt** is indicated as **15KV/us**. The **ID** is indicated as **100A/div**. The **VDS** is indicated as **200V/div**. The time scale is **t : 100ns/div**. A thumbs up icon and the text **GOOD!** are present.

Miller clamp circuit

The top diagram shows the Miller clamp circuit for a 2DMBxxxxxxCC. It includes a timing control block, VCC, VEE, and nodes VOHx, VOLx, MCLx, and COMx. A red dashed line indicates a signal path from COMx to MCLx. The bottom diagram shows the timing waveforms for VDS (blue) and VGS (purple). VDS has a sharp spike during the VGS pulse. A blue arrow points to a small spike on the VGS waveform, with the text "No malfunctions" indicating that this spike is not a problem.

Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules

1-4. Features of Gate Driver Modules

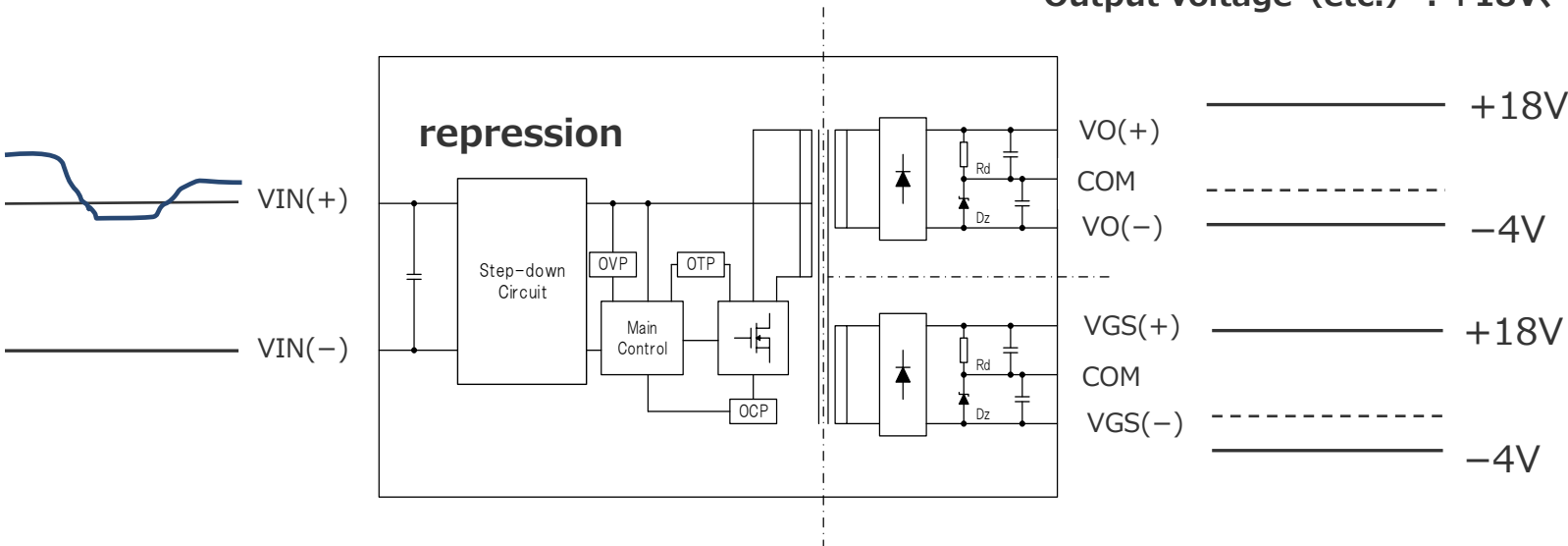
Feature③ $V_{GS}(+)$: On resistance does not decrease at 15V
 $V_{GS}(-)$: Low tolerance (Less than $-7V$)

--- IGBT's Gate driver cannot be used

Support with a gate driver ... Constant voltage control of V_{GS}

Input voltage : 13V~28V

Output voltage (etc.) : +18V, -4V



Controls the gate voltage to be constant even for input fluctuations
 The gate voltage is constant even for output fluctuations
 (SW frequency, QG of power module)

**Improved SiC reliability
 Low loss operation**

Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules

1-4. Features of Gate Driver Modules

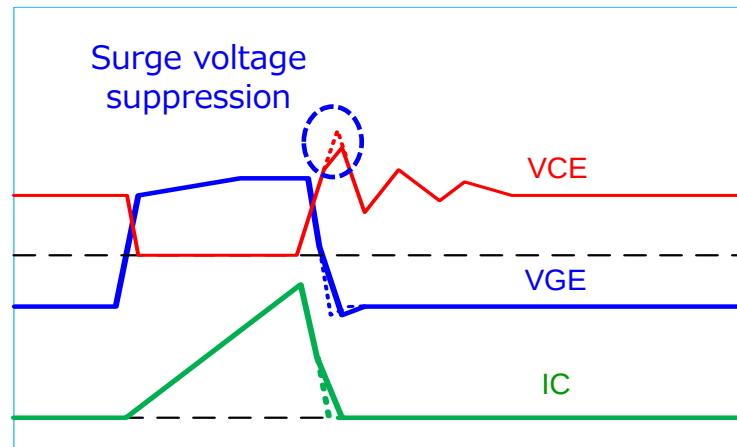
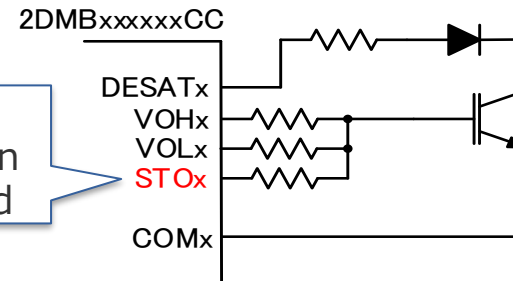
Feature④ dV/dt can be set high

----- Turn-on: Recovery current is small
Turn-off: No tail current

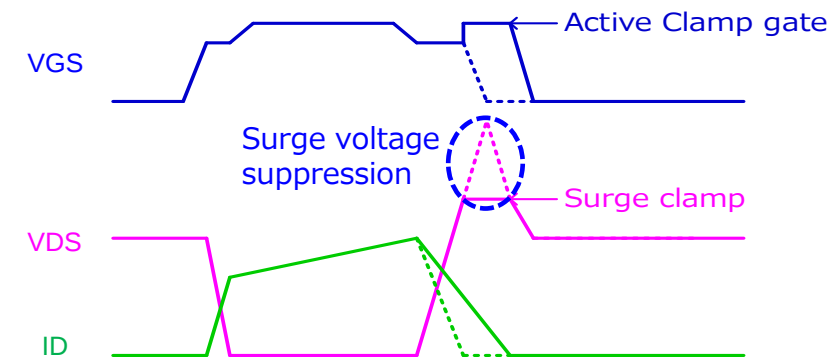
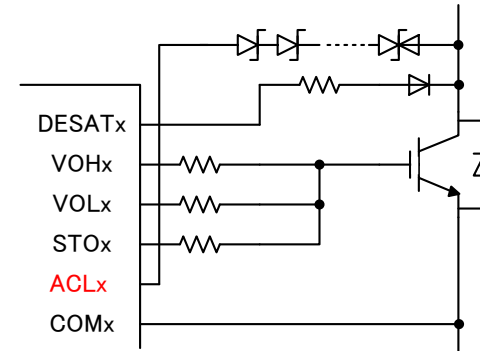
Support with a gate driver ... Ability to suppress surge voltage with high dV/dt
(Soft turn-off, Active clamp)

Soft turn-off

Soft turn-off
Operates when
short-circuited



Active clamp (Option)



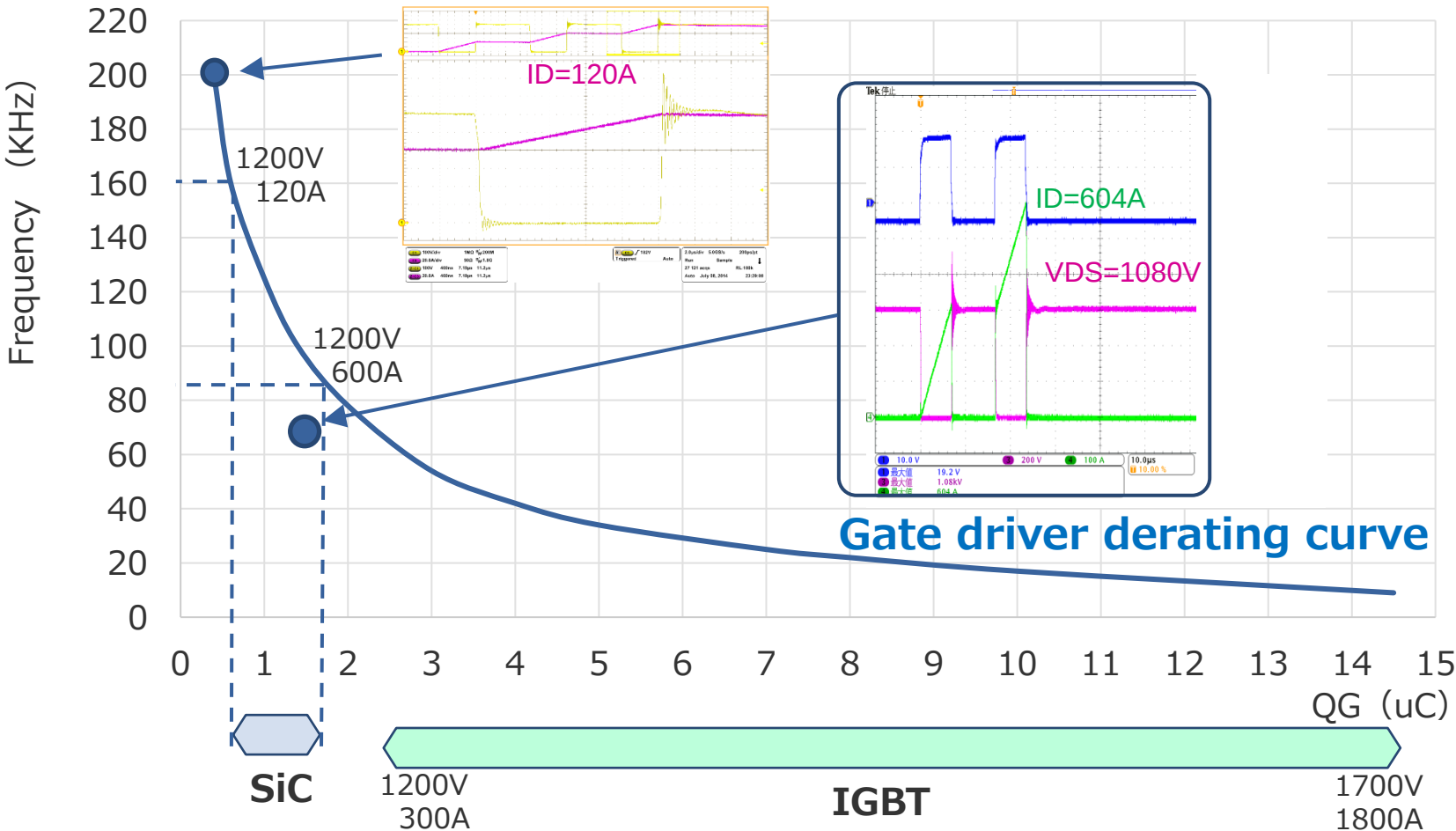
Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules

1-4. Features of Gate Driver Modules

Feature⑤ High frequency operation is possible

----- Drive power needs to be increased

Support with a gate driver ... Output capacity considering SiC power module



Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules

1-5. Gate drive waveform of SiC power module (2 Pulse test)

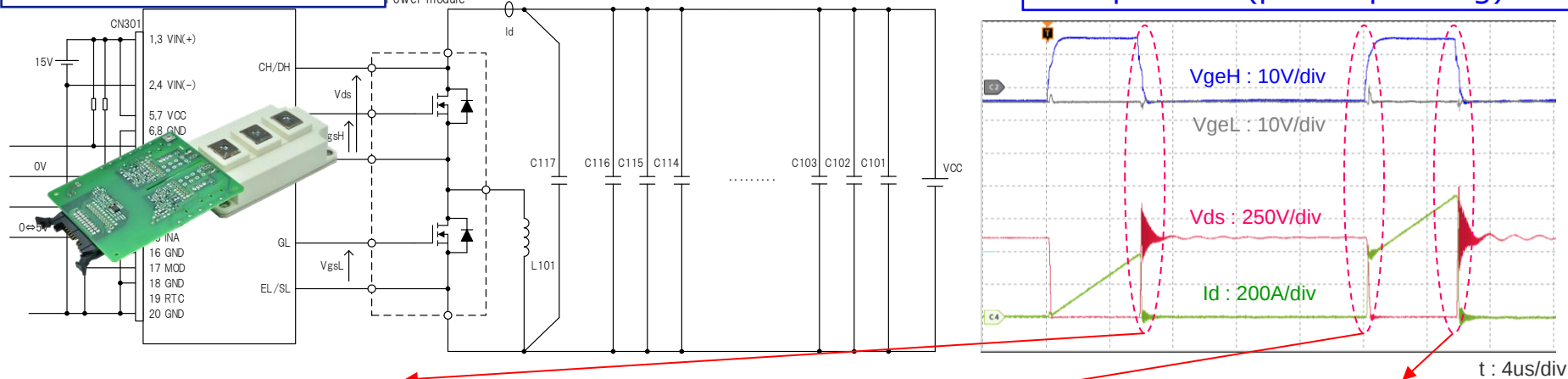
SiC MOSFET : FF3MR12KM1

DC Link : 600V, Ron : 4.3Ω, Roff : 3.6Ω, Upper arm, Tj=25°C

2CG010BBC15N+ Evaluation board

C101-116 : 560uF(Ls : 60nH)
C117 : 1uF(Ls : 20nH)

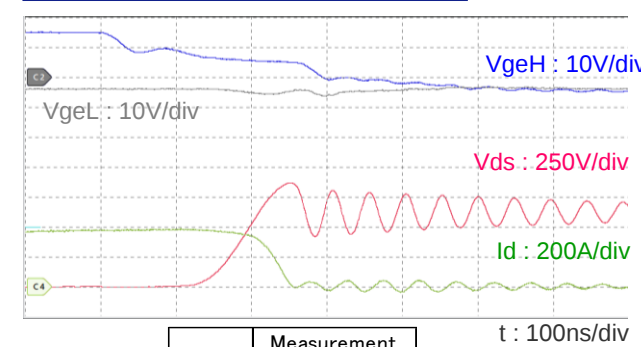
Highly stable gate drive with proprietary drive circuit and miller clamp circuit (patent pending)



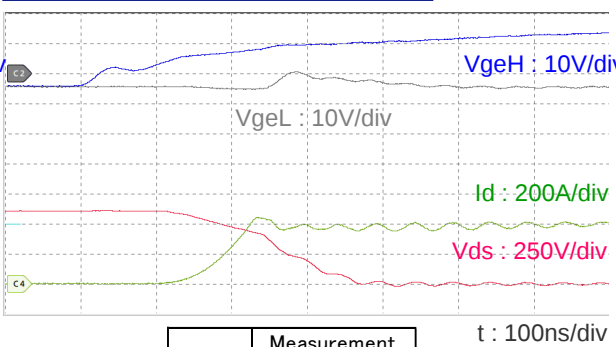
Turn OFF / Ic =375A

Turn ON / Ic =375A

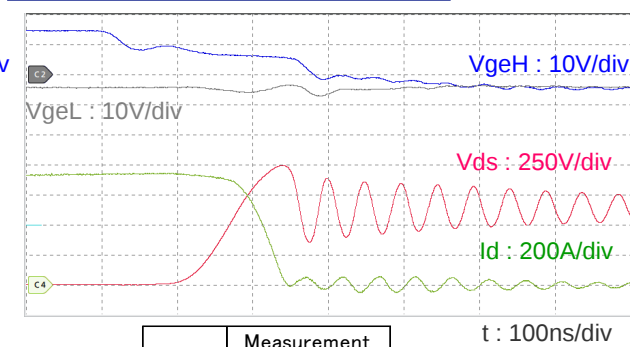
Turn OFF / Ic =750A



Item	Measurement value	
Vdsp	866	V
dV/dt	8.8	kV/us
di/dt	6.2	kA/us
Eoff	13	mJ



Item	Measurement value	
dV/dt	4.6	kV/us
di/dt	5.0	kA/us
Eon	19	mJ



Item	Measurement value	
Vdsp	992	V
dV/dt	9.2	kV/us
di/dt	10.3	kA/us
Eoff	33	mJ

Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules

1-5. 2 Pulse test (Enlarged waveform)

SiC MOSFET : FF3MR12KM1

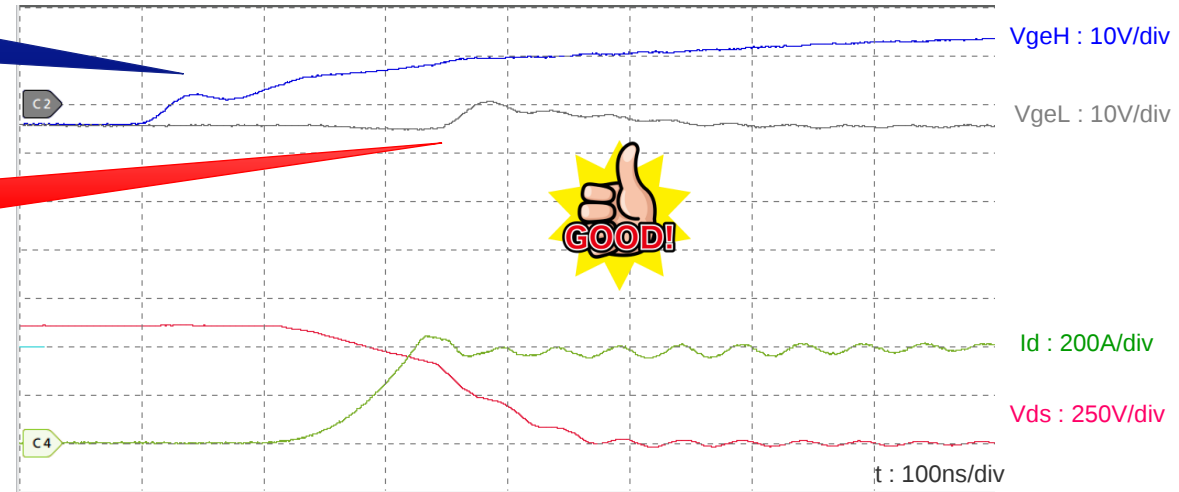
SW side gate (turn ON)
No ringing and no overshoot

OFF side gate
Stable L state without malfunction

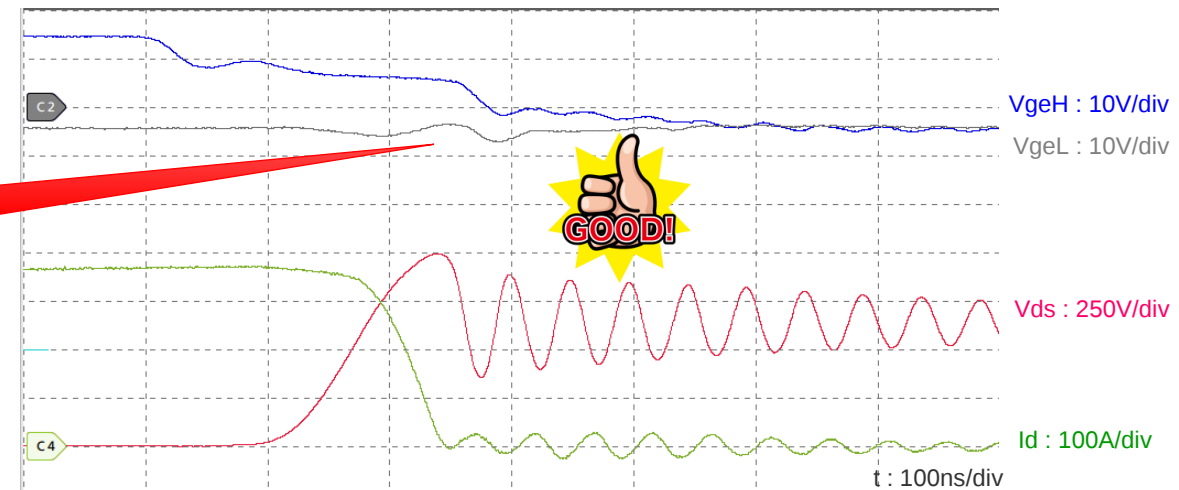


OFF side gate
Stable L state without malfunction

Turn ON / $I_c = 375A$



Turn OFF / $I_c = 750A$



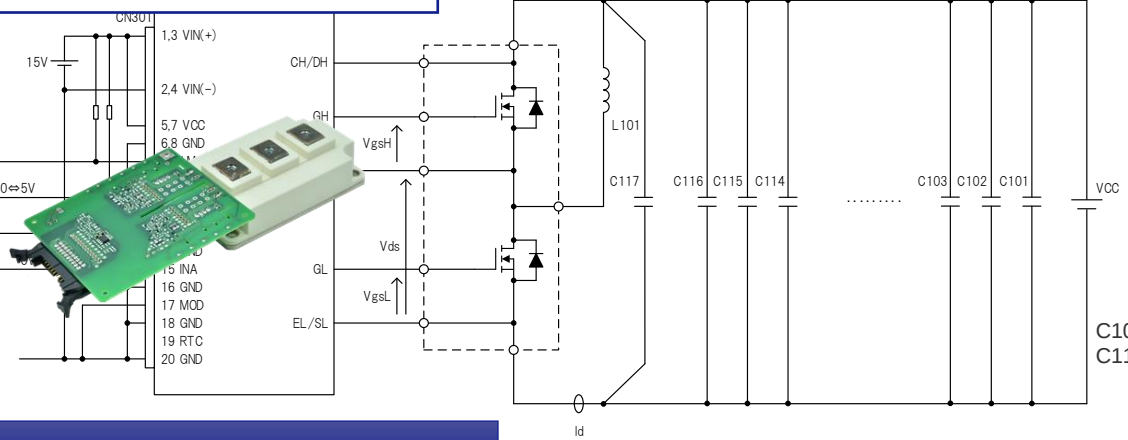
Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules

1-5. Gate drive waveform of SiC power module (Short circuit test)

SiC MOSFET : FF3MR12KM1

DC Link : 600V, Ron : 4.3Ω, Roff : 3.6Ω, Lower arm, Tj=25°C

2CG010BBC15N+ Evaluation board



This driver suppresses the Vds peak voltage in the short circuit by our original circuit technology, and can control the mask time to prevent false short circuit detection. (Patent pending)

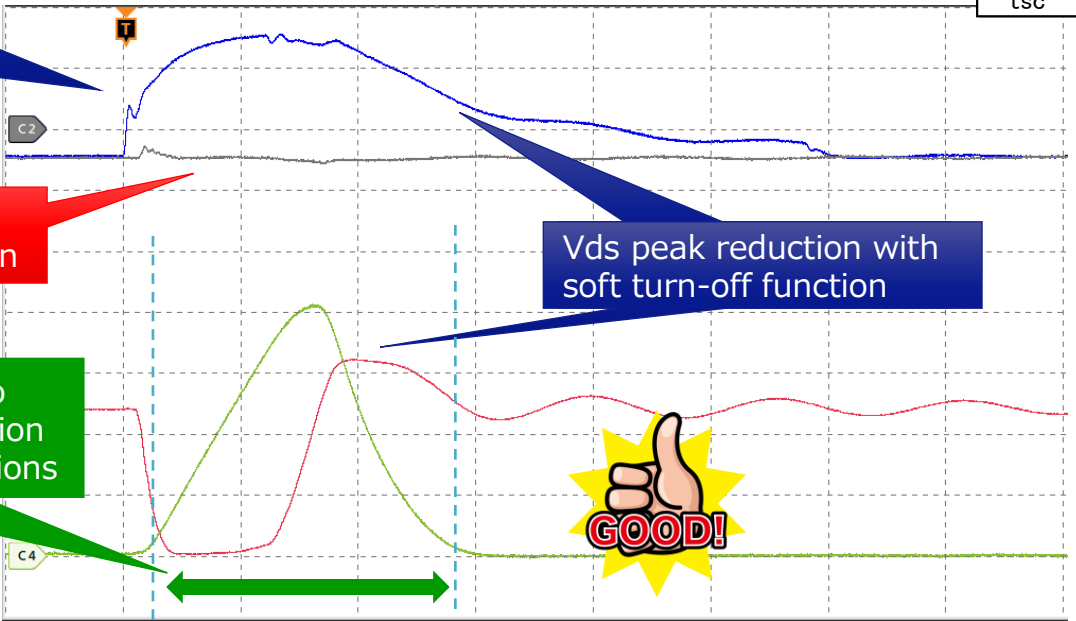
C101-116 : 560uF(Ls : 60nH)
C117 : 1uF(Ls : 20nH)

Item	Measurement value	
Vdsp	806	V
Idp	4124	A
tsc	2.28	us

SW side gate (turn ON)
No ringing and no overshoot

OFF side gate
Stable L state without malfunction

Constant control of mask time to prevent false short circuit detection regardless of short circuit conditions



VgeL : 10V/div

VgeH : 10V/div

Vds : 250V/div

Id : 1kA/div

t : 1us/div

Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules



1-6. Comparison and expansion

Advantage of Tamura Gate driver modules (2CG-B / 2CG-D)

Item	TAMURA	Company A (4W)	Advantages
Power module	SiC-MOSFET /IGBT	IGBT	○
Input Voltage	13.5-26.4V	14.5-15.5V	○
Output Voltage	+15V/-10V +15V/-15V +18V/-4V +18V/-2V +15V/-4V	+15V/-10V	○
Peak output current	±43A	±35A	○
Frequency	150kHz (Max)	100kHz (Max)	○
Isolation capacitance	12pF(TYP)	22pF	○
CMTI	70kV/us	50kV/us	○
Protection	Soft turn off Active Clamp Miller Clamp	Active Clamp	○

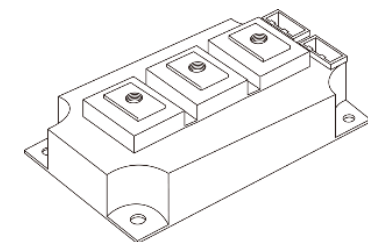
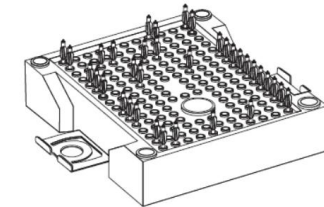
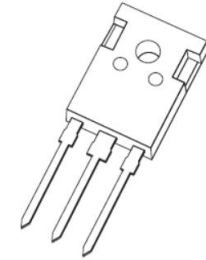
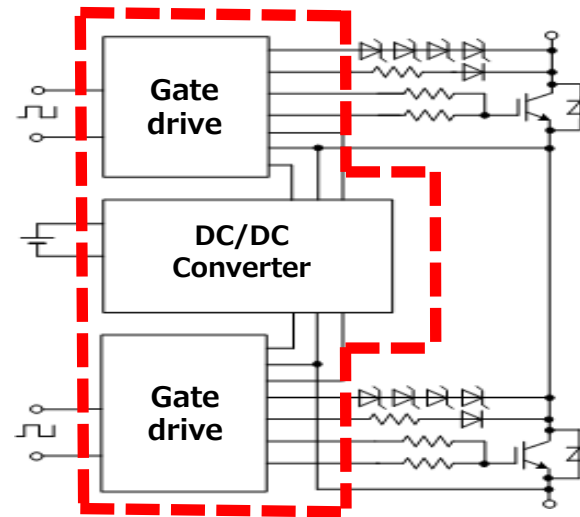
Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules

1-6. Comparison and expansion

Deployment example of Tamura Gate driver modules (2CG-B / 2CG-D)



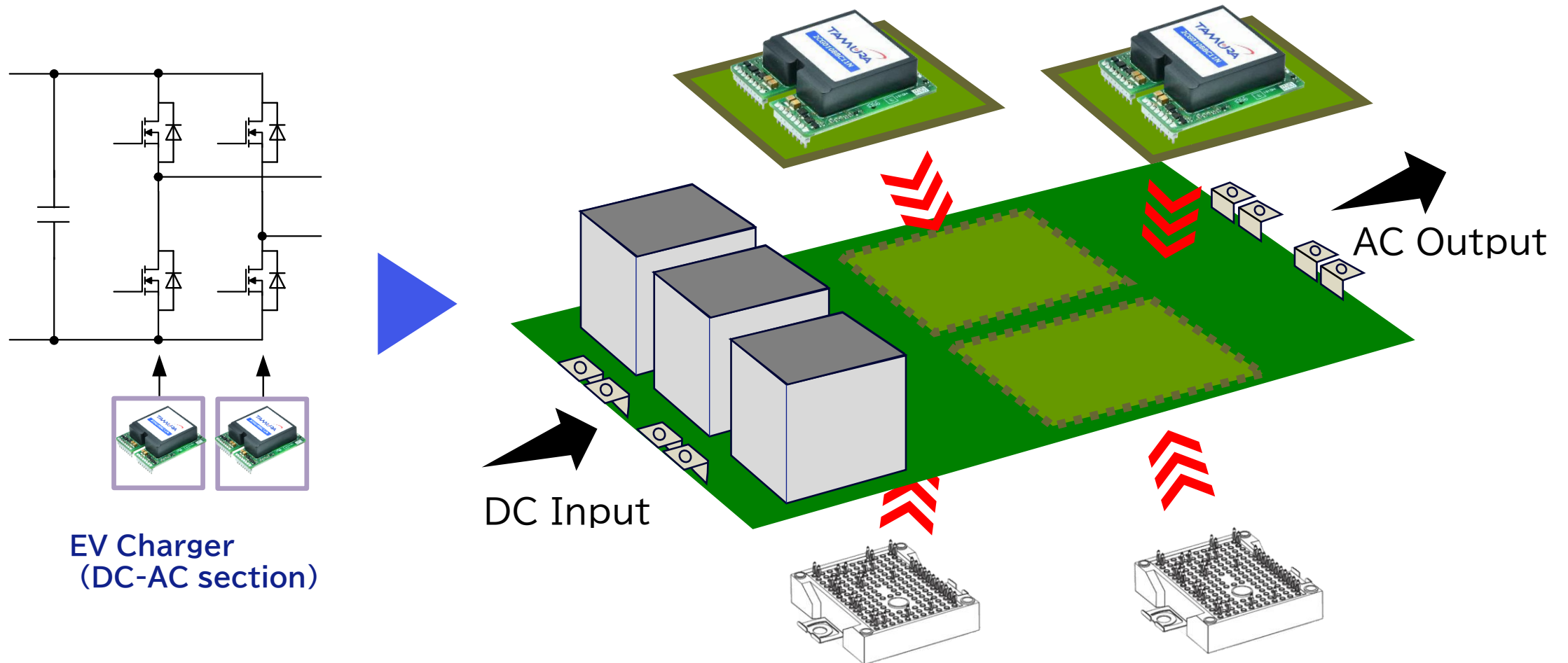
Gate Driver Module



Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules

1-6. Comparison and expansion

Deployment example of Tamura Gate driver modules (2CG-B / 2CG-D)



Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules



1-7. Product Line-up

Gate Driver Module 2CG-B / 2CB-D series

		MODEL					
		2CG010BBC11N	2CG010BBC12N	2CG010BBC13N	2CG010BBC14N	2CG010BBC15N	2CG010DBC11N
Output	Output voltage(+)	+15V	+15V	+18V	+18V	+15V	+15V
	Output voltage(-)	-10V	-15V	-4V	-2V	-4V	-10V
	Output power/1ch	4.0W	3.3W	3.5W	3.2W	3.0W	4.0W
	Number of output	2					
	Peak output current	±43A					
Input	Input voltage	DC13~28V					
	Logic input voltage	DC3.3V, 5V					
Insulation	Withstand voltage	Primary to secondary AC5KV / Secondary to secondary AC4KV					
	Partial discharge extinction voltage	2400V peak or more					
Function	Mode select	Direct mode / Half bridge mode					
	DESAT protection	Yes					
	Soft turn off	Yes					
	Active clamp	No					Yes
	Miller clamp	Yes					No

Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules

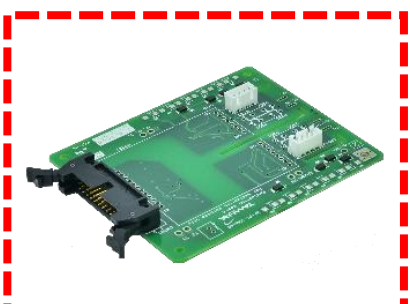
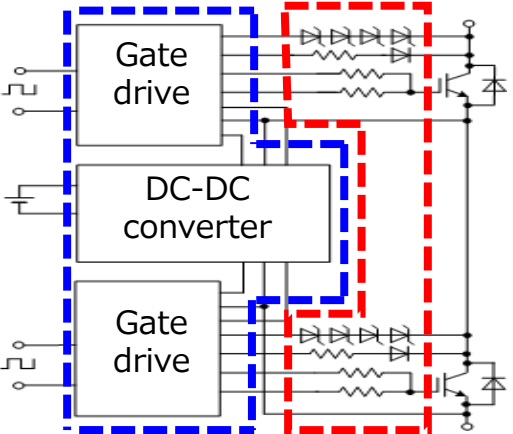
1-7. Product Line-up for EconoDUAL™ and 62mm type

Package	IDN	Part No	TAMURA Driver				
			Evaluation board	2CG-B	2DD		
	V _{DS} = 1200V						
	180	FF6MR12KM1H		2RB020BB	2CG010BBC13N (+18/-4V) 	2DD180407C (+18V/-4V) 	
		FF6MR12KM1HP					
	280	FF3MR12KM1H					
		FF3MR12KM1HP					
	420	FF2MR12KM1H					
		FF2MR12KM1HP					
	560	FF1MR12KM1H					
		FF1MR12KM1HP					
	V _{DS} = 2000V						
		200	FF5MR20KM1H		2RB020BB	2CG010BBC13N (+18/-4V) 	2DD180407C (+18V/-4V) 
			FF5MR20KM1HP				
		300	FF4MR20KM1H				
			FF4MR20KM1HP				
400		FF3MR20KM1H					
		FF3MR20KM1HP					

I_{DN} :Implemented drain current



Gate Driver Module
(2CG-B series)



Evaluation board
(2RB series)



Can be connected directly !

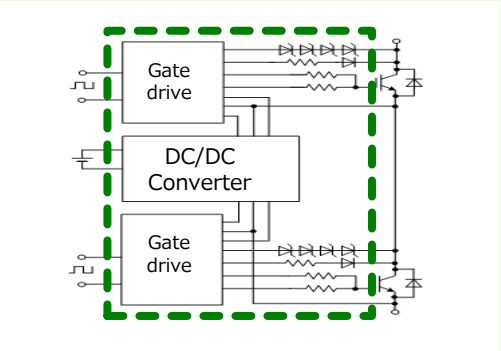
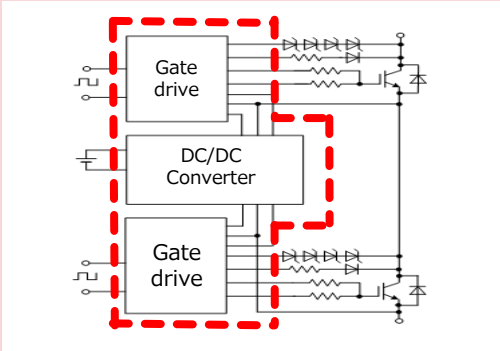
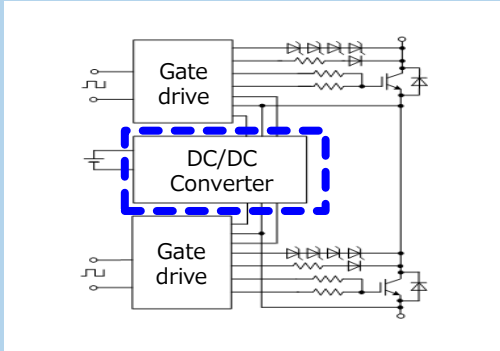
Gate drivers that bring out the performance of Infineon Technologies AG SiC Power Modules

1-7. Product Line-up for EconoDUAL™ and 62mm type

Package	I _{DN}	Part No	Gate Driver Unit	Gate Driver Module	DC-DC
			2EG-B 	2CG-B 	2DD 
V_{DS} = 1200V					
	500	FF1MR12MM1H_B11*	2EG01XBxN13N	2CG010BBC13N	2DD180407C

*The gate driver is not press-fit compatible, so please solder it.

x: Signal input voltage selectable “C” => 3.3~15V “D” => 15V

Product Function	Gate Driver Unit Gate Driver Module + Gate resistors Protective function 	Gate Driver Module DC/DC Converter + Gate drive 	DC/DC Converter 2in1 PM designated DC/DC Converter 
Block diagram			

Index

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(SiC Power Module : FF3MR12KM1)
- 1-6. Comparison and expansion
- 1-7. Product Line-up for EconoDUAL™ and 62mm type

2) Introduction of One Tamura

Appendix) Contact person

Introduction of One Tamura (General application)

Device technology

Ga_2O_3



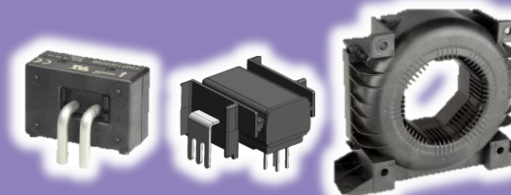
Novel Crystal Technology, Inc.

Gate driver Circuit technology



Gate Driver Unit

Module technology Current sensor



Soldering technology



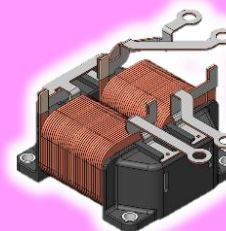
Electric Chemicals
Soldering material
Die attach material
TIM material

Power electronics technology and main products

Reflow soldering system



Automotive reactor



Reactor for PF
(2 in 1)

Passive components

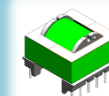


Reactor Trans Coil

Large reactor/
transformer



Toroidal coil



SW-Trans

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Digi-Key



Mouser



Energize the Future 100th

CORPORATE GOVERNANCE REPORT



Tamura's mascot "Quenu"